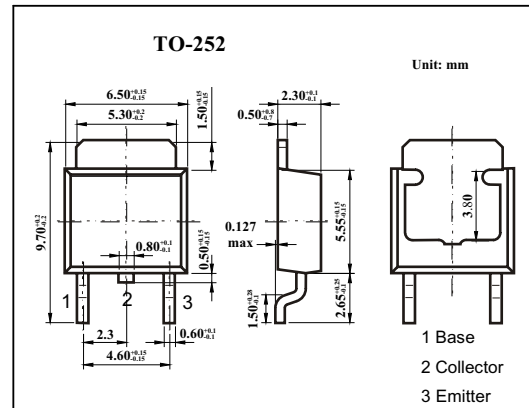


## NPN Silicon Power Transistor 2SD882

### ■ Features

- Collector Power Dissipation:  $P_c=1.25W$
- Collector Current:  $I_c=3A$



### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	40	V
Collector to Emitter Voltage	$V_{CEO}$	30	V
Emitter to Base Voltage	$V_{EBO}$	5	V
Collector Current to Continuous	$I_c$	3	A
Collector Dissipation	$P_c$	1.25	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ C$

### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_c=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_c=10\text{ mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E=100\mu A, I_c=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40\text{ V}, I_E=0$			1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=30\text{ V}, I_B=0$			10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6\text{ V}, I_c=0$			1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=2\text{ V}, I_c=1\text{ A}$	60		400	
		$V_{CE}=2\text{ V}, I_c=100\text{ mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=2\text{ A}, I_B=0.2\text{ A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c=2\text{ A}, I_B=0.2\text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE}=5\text{ V}, I_c=0.1\text{ mA}, f=10\text{ MHz}$	50			MHz

### ■ $h_{FE}$ Classification

Rank	R	Q	P	GR
$h_{FE}$	60~120	100~200	160~320	200~400

### ■ Marking

Marking	D882